



Description

The TD101X series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector in a plastic LSO package with the robust coplanar double mold structure. TD101X series provide the most stable isolation feature.

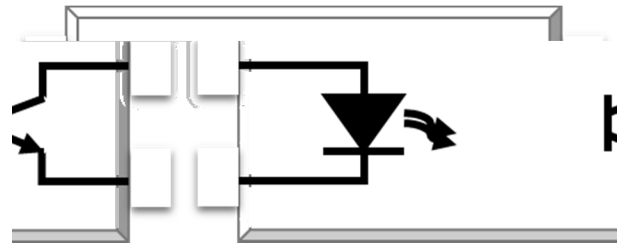
Features

- High isolation (000) * +S
- Temperature stability available see order information
- D, input with transistor output
- Operating temperature range . ((/ , to 110 / ,
- $I_{SO} \leq 1A$, ' , compliance
- +SL class 1
- Regulatory Approvals
 - 2L . 2L1(33)
 -)D1 . 14503!3.(.(6)D1077!. (8
 - , 9 , : G ; !<! = #1% G ; 77<7

Applications

- Switch mode power supplies
- Programmable controllers
- Household appliances
- Office equipment

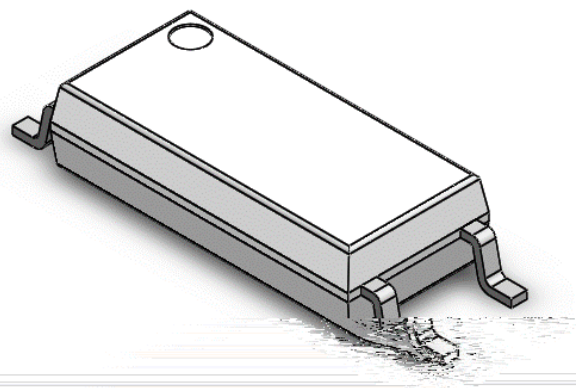
SCHEMATIC



PIN DEFINITION

1. Anode
2. Cathode
3. Emitter
4. Collector

PAC A ! E O " T # I N E





A ' SO# " TE MA (IM " M) ATIN ! S				
A * A+ 1T1 *	S@+ ; OL)AL21	24AT	4OT1
A4 2T				
Borward , urrent	A _B	50	mA	
ea" Borward , urrent	A _B	1	A	1
* e&erse)oltage) *	5)	
Anput ower Dissipation	A	100	m\$	
O2T 2T				
, ollector . 1mitter)oltage) , 10	70)	
1mitter . , ollector)oltage) 1, 0	3)	
, ollector , urrent	A,	(0	mA	
Output ower Dissipation	o	1(0	m\$	
, O+ +O4				
Total ower Dissipation	tot	?(0	m\$	
Asolation)oltage) iso	(000) rms	?
Operating Temperature	Topr	. ((C110	/,	
Storage Temperature	Tstg	. ((C1?(/,	
Soldering Temperature	Tsol	?50	/,	

Note 1. 100µs pulse, 100 ! "#e\$uenc%

Note 2. A& 'o# 1 ()nute, R. . * +0 , -0.



ELECTRICAL CHARACTERISTICS at Ta=25°C							
Symbol	Unit	Min	Typ	Max	Test Conditions	Notes	Ref
Forward Voltage	V _F	-	1.5	-	I _F = 10 mA, I _R = 0	-	-
Reverse Current	I _R	-	10	-	V _R = 5 V, I _F = 0	-	-
Input Capacitance	C _{in}	-	0	-	f = 1 MHz, V _R = 0 V	-	-
Collector Current	I _C	-	100	-	V _{CE} = 5 V, I _B = 10 mA	-	-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	0.7	-	I _C = 10 mA, I _B = 10 mA	-	-
Collector-Emitter Voltage	V _{CE}	-	3	-	I _C = 10 mA, I _B = 10 mA	-	-
Transfer Ratio	h _{FE}	-	50	-	I _C = 10 mA, I _B = 1 mA	-	-
Transfer Ratio	h _{FE}	-	5	-	I _C = 10 mA, I _B = 100 μA	-	-
Transfer Ratio	h _{FE}	-	100	-	I _C = 10 mA, I _B = 100 μA	-	-
Transfer Ratio	h _{FE}	-	150	-	I _C = 10 mA, I _B = 100 μA	-	-
Transfer Ratio	h _{FE}	-	?	-	I _C = 10 mA, I _B = 100 μA	-	-
Transfer Ratio	h _{FE}	-	?	-	I _C = 10 mA, I _B = 100 μA	-	-
Transfer Ratio	h _{FE}	-	?	-	I _C = 10 mA, I _B = 100 μA	-	-
Transfer Ratio	h _{FE}	-	?	-	I _C = 10 mA, I _B = 100 μA	-	-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	0.1	-	I _C = 10 mA, I _B = 10 mA	-	-
Isolation Resistance	R _{ISO}	10 ¹¹	10 ¹¹	-	V _R = 50 V, I _C = 0	-	-
Bloating Capacitance	C _{BO}	-	0	-	f = 1 MHz, V _R = 0 V	-	-
Cut-off Frequency	f _c	-	70	-	V _{CE} = 5 V, I _C = 10 mA, I _B = 10 mA	-	-
Response Time (t _{rise})	T _r	-	17	-	V _{CE} = 5 V, I _C = 10 mA, I _B = 10 mA	-	-
Response Time (t _{fall})	T _f	-	5	-	V _{CE} = 5 V, I _C = 10 mA, I _B = 10 mA	-	-

Note 1. V_F = 0.121 V
 Note 2. V_{CE(sat)} = 0.1 V





CHARACTERISTICS - ES

<p>Fi..1 Forward Current 0\$. Ambient Temperature</p>	<p>Fi..2 Collector Power Dissipation 0\$. Ambient Temperature</p>
<p>Fi..3 Forward Current 0\$. Forward Voltage</p>	<p>Fi..4 Collector Dark Current 0\$. Ambient Temperature</p>

Fi..+ Collector Current
0\$. Collector Emitter Voltage

Fi..4 Collector Current
0\$. Collector Emitter Voltage 2.81416 (2.81416 (2.1

CHARACTERISTICS - ES

Fig. 5 Normalized Current Transfer Ratio vs. Forward Current

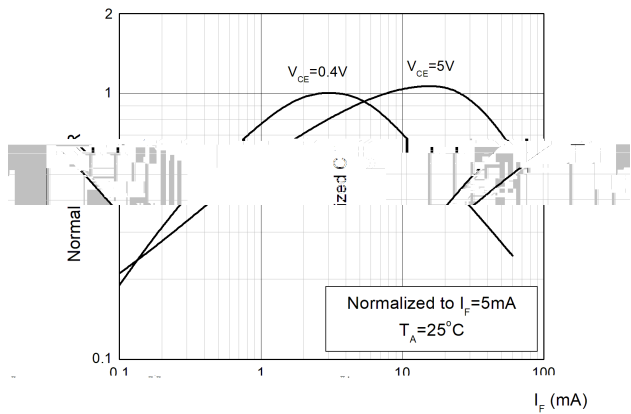


Fig. 8 Normalized Current Transfer Ratio vs. Ambient Temperature

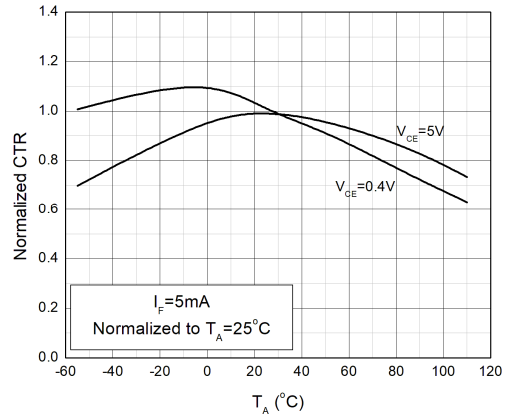


Fig. 9 Collector-Emitter Saturation Voltage vs. Ambient Temperature

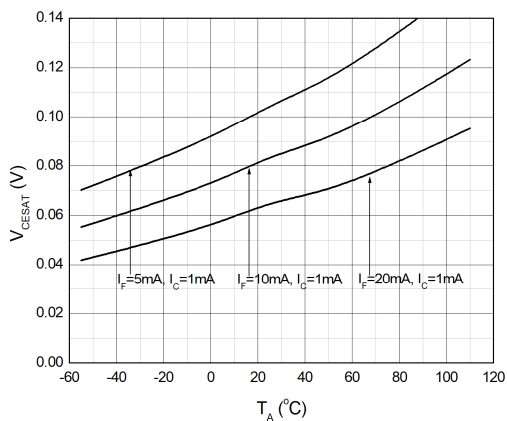


Fig. 10 Switching Time vs. Load Resistance

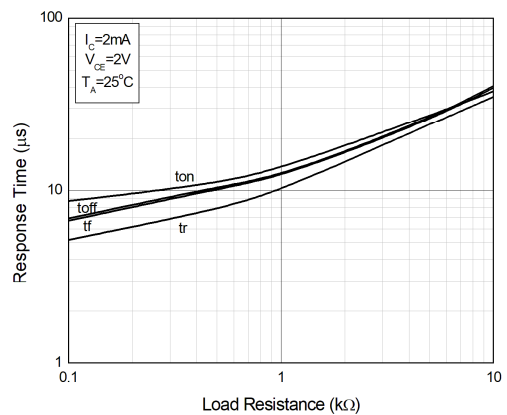
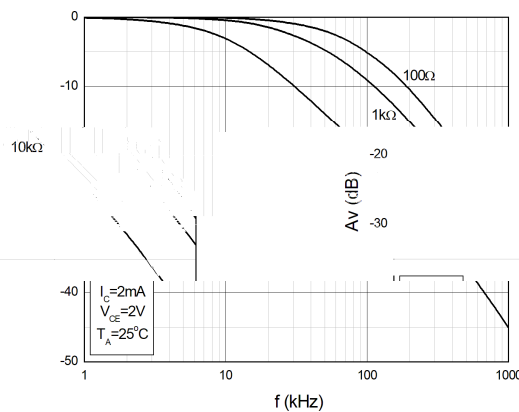


Fig. 11 Frequency Response



TEST CIRCUITS

Fig. 12 Test Circuit of Forward Time

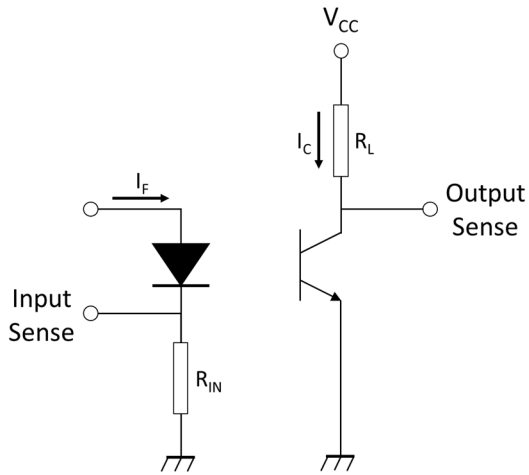


Fig. 13 Characteristic of Forward Time

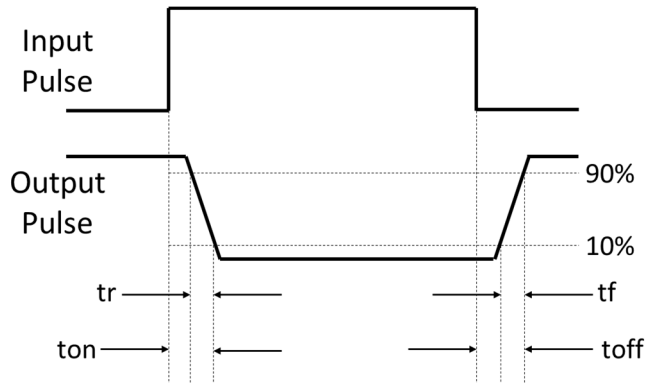
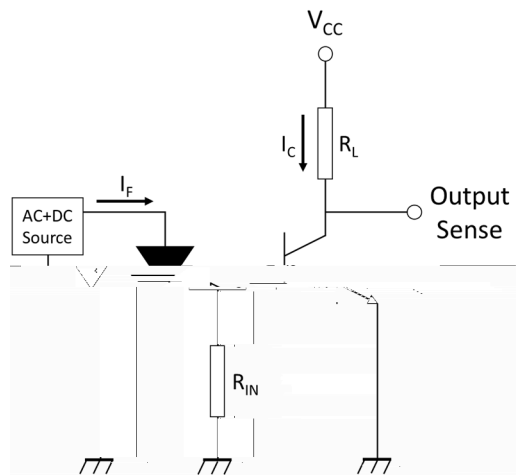
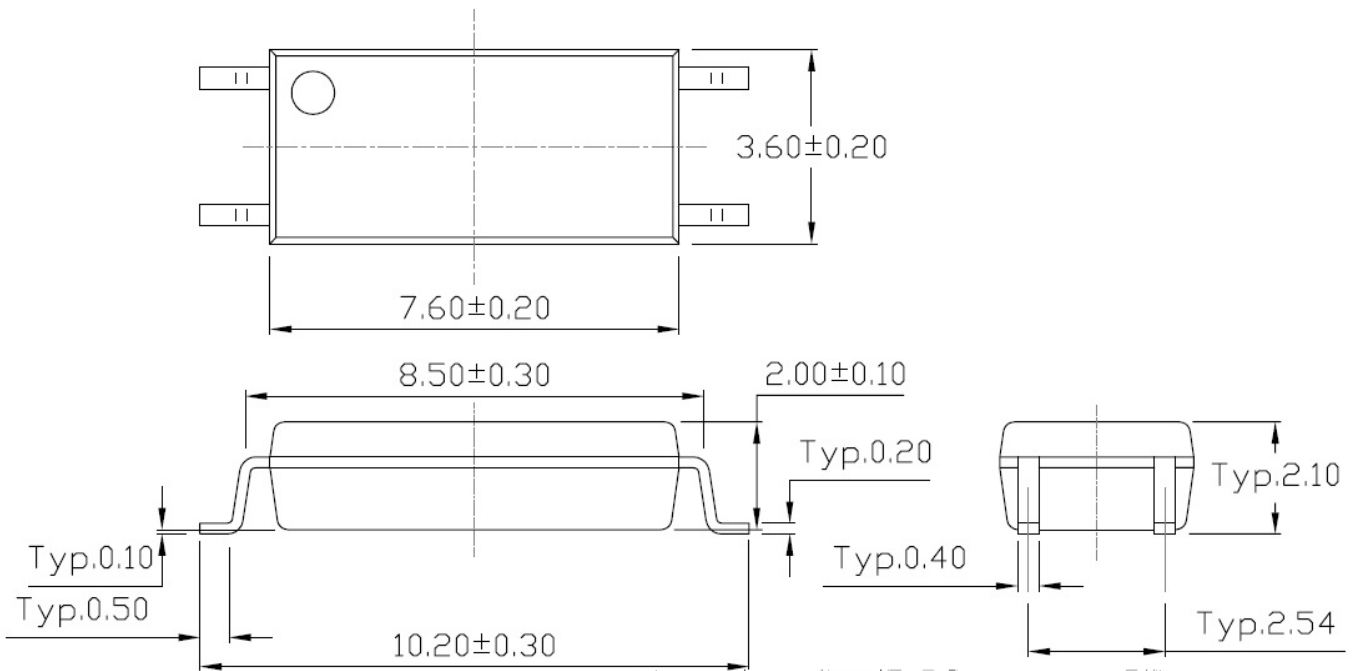


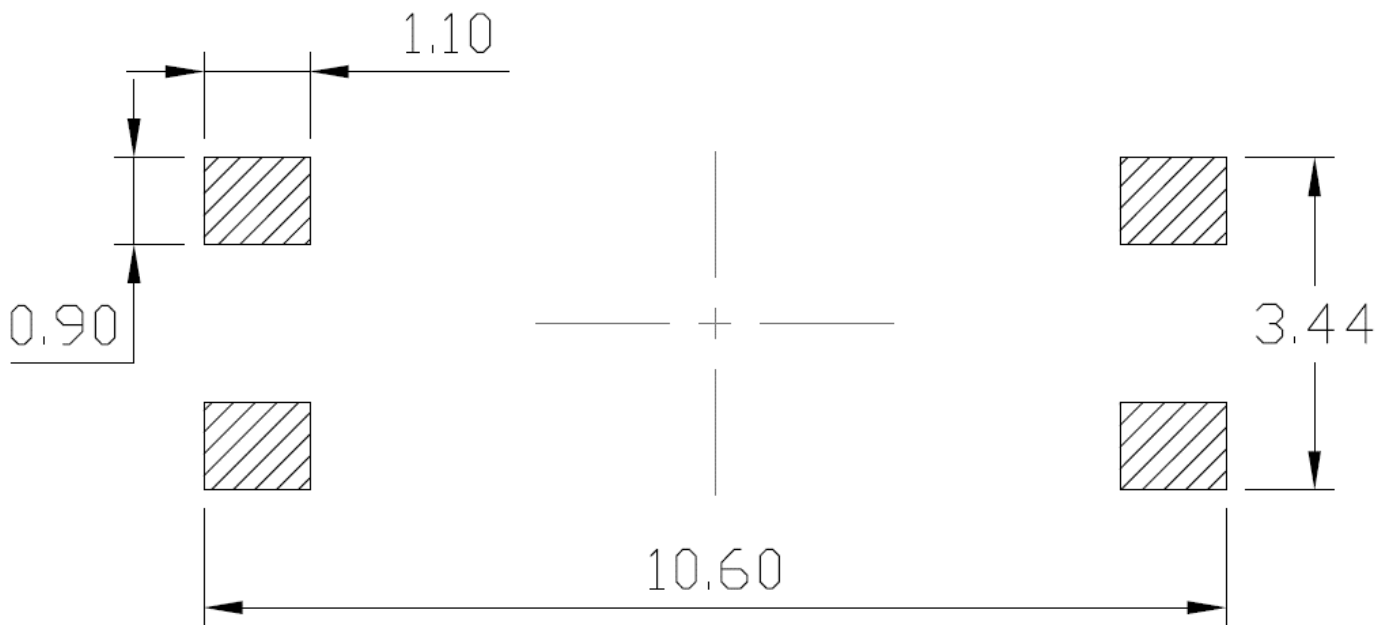
Fig. 14 Test Circuit of Reverse Time



PAC A! E DIMENSIONS Dimension\$ in mm &le\$\$ other / i\$e \$tated=

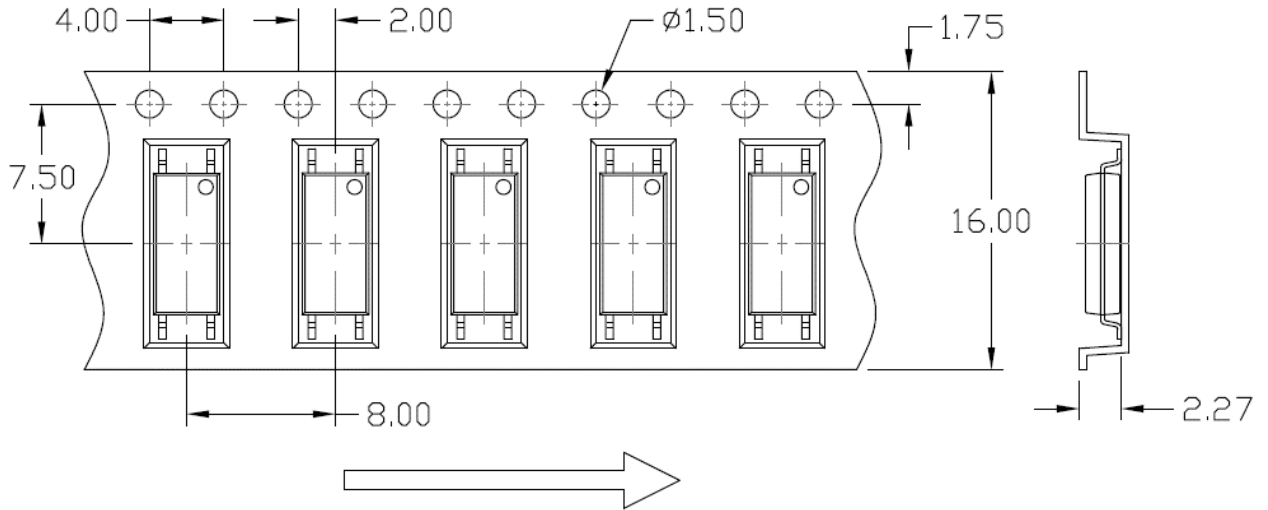


RECOMMENDED SIDE MOUNTING DIMENSIONS Dimension\$ in mm &le\$\$ other / i\$e \$tated=

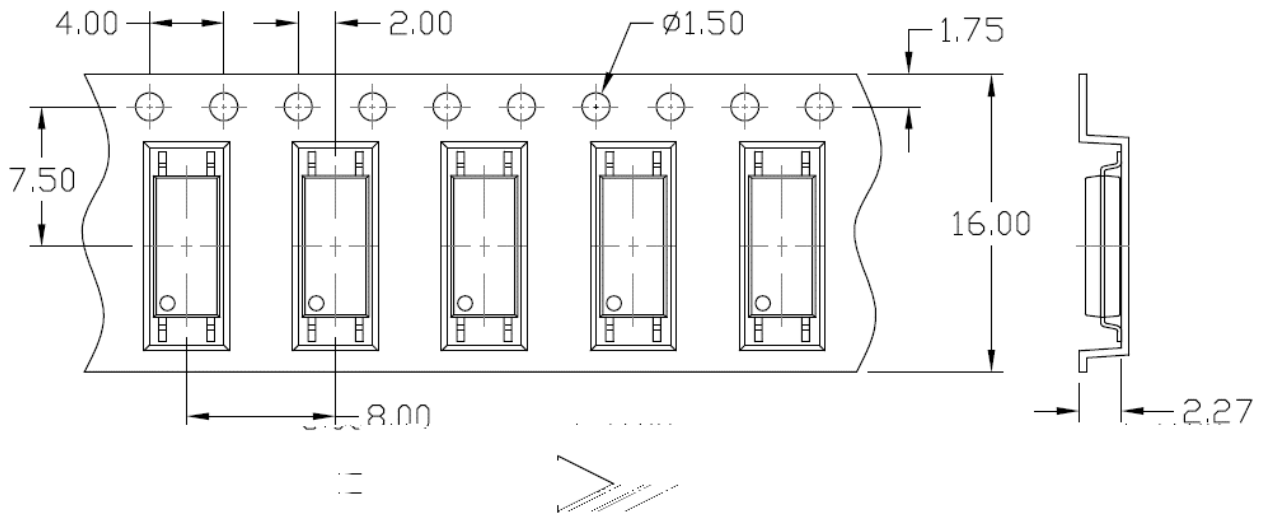


CA)) IE) TAPE SPECIFICATIONS Dimension\$ in mm &nle\$\$ other / ise \$stated=

O%tion T1

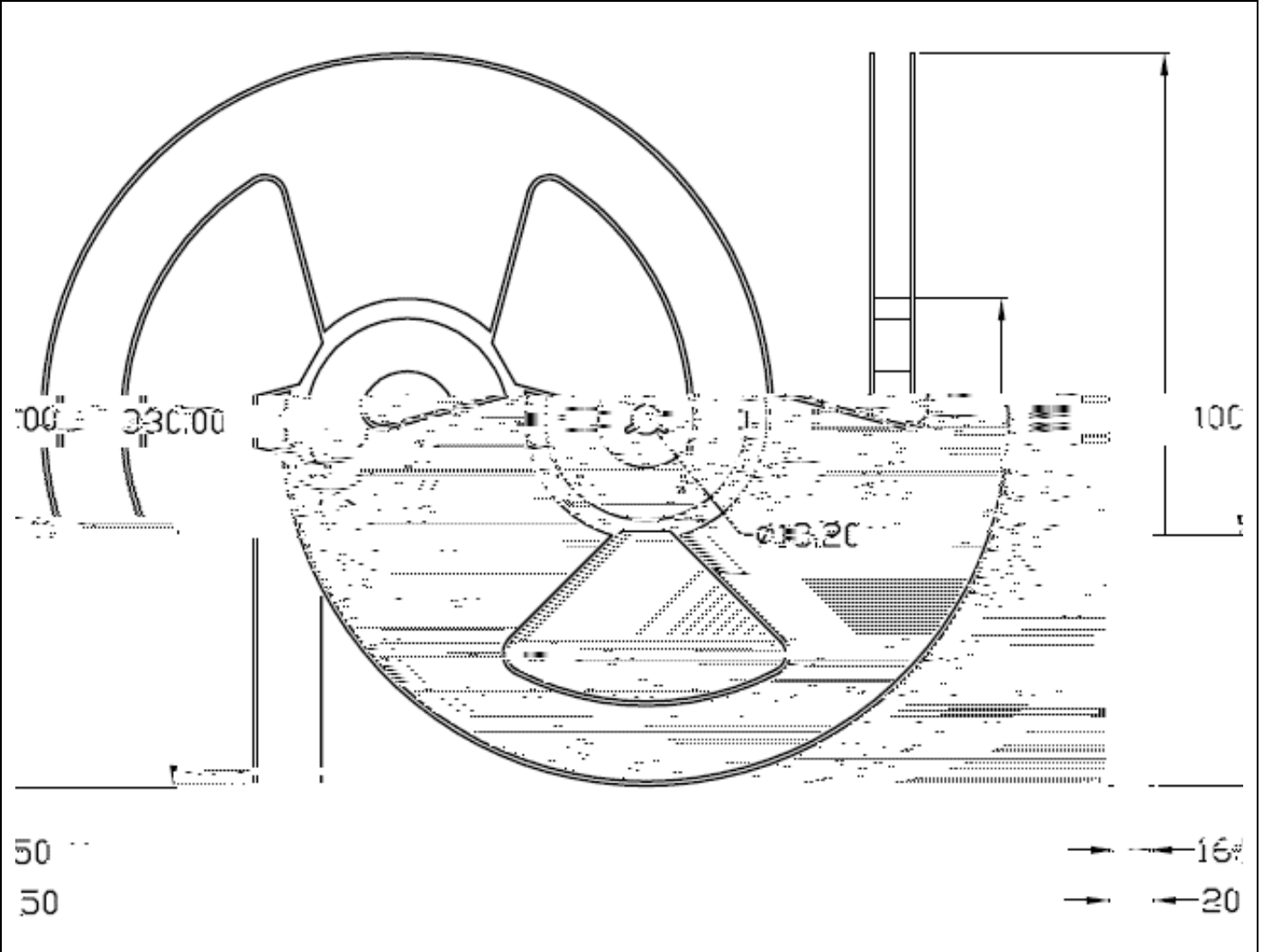


O%tion T2





EE# SPECIFICATIONS Dimension\$ in mm &nle\$\$ other / i\$e \$tated=
O%tion T1 > T2





' O (SPECIFICATIONS) eel T<%e=

Inner ' o?

23 W 3 * /-cm 3 /-cm 3 -.9cm

O&ter ' o?

CODE IN! AND MA) IN! INFORMATION

MA) IN! INFORMATION



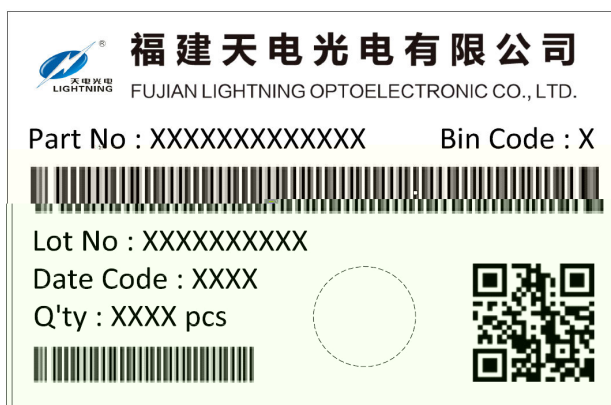
TD @ Company Abbr.
1:1 (@ Part Number
- @ -DE Option
A @ Fiscal Year
A @ Manufacturing Code
B B @ Board Bee2

CODE IN! INFORMATION

#A 'E# INFORMATION

TD1:1 (CD=3! -

TD : , company Abbr#
101X : *an" 60J1J?J=J!J(J5J3J7J<8
K : Tape and *eel Option 6T1JT?8
G : Green
) :)D1 Option 6) or 4one8



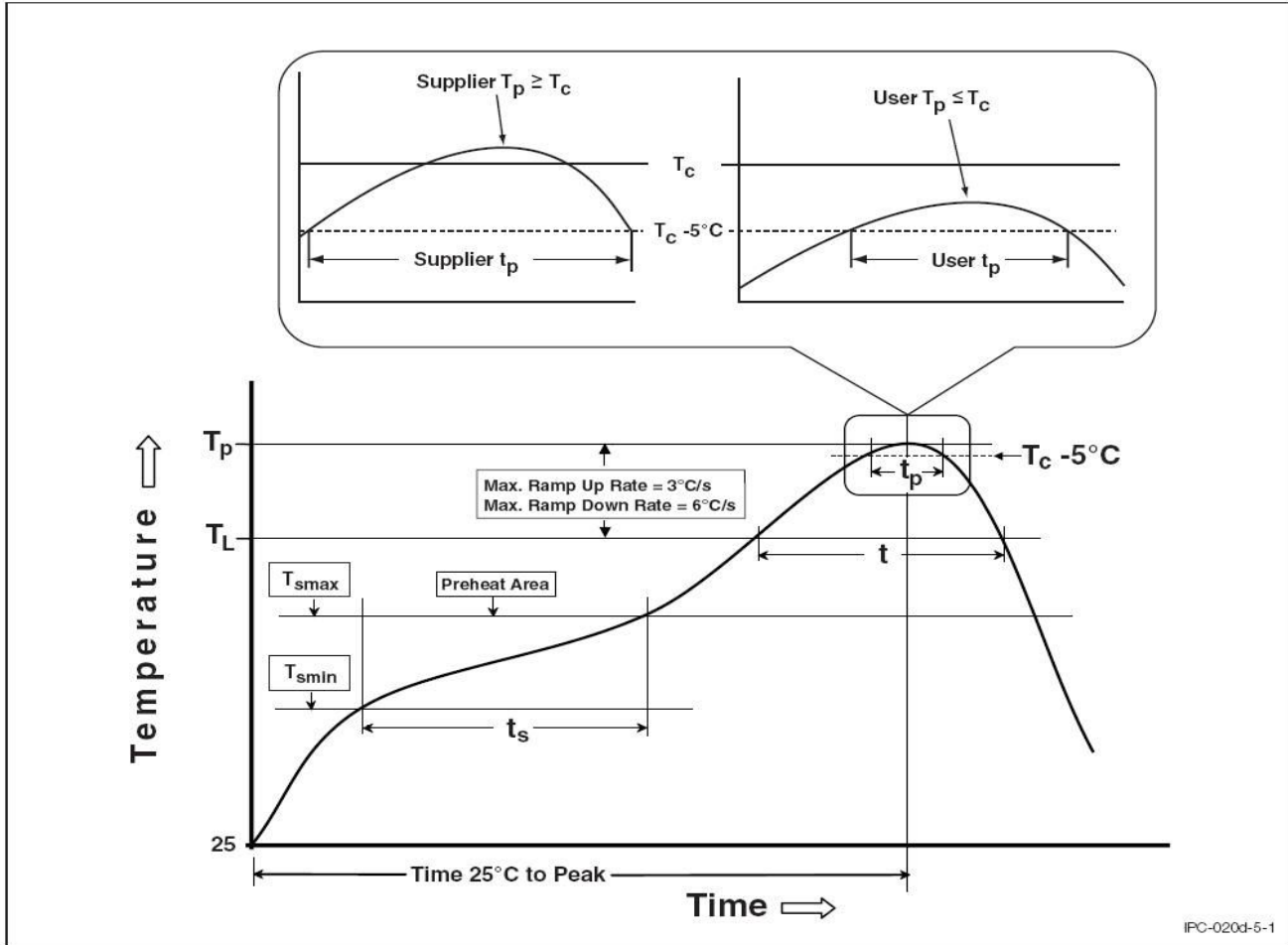
福建天电光电有限公司
 FUJIAN LIGHTNING OPTOELECTRONIC CO., LTD.
 Part No : XXXXXXXXXXXXX Bin Code : X
 Lot No : XXXXXXXXXXXX
 Date Code : XXXX
 Q'ty : XXXX pcs

PAC IN! E " ANTITA

Option	E&antit<	E&antit< F Inner 1o?	E&antit< F O&ter 1o?
T1	=000 2nits! *eel	= *eels!Anner bo-	(Anner bo-JOuter bo- D ! (" 2nits
T?	=000 2nits! *eel	= *eels!Anner bo-	(Anner bo-JOuter bo- D ! (" 2nits

TEST PROFILE INFORMATION

TEST PROFILE #



IPC-020d-5-1

Profile Feature	Sn3Pb Assembly Profile	PbFree Assembly Profile
Temperature +in# T_{smin}	100	100
Temperature +a-# T_{smax}	100	100
Time t_s from T_{smin} to T_{smax}	50.1±0 seconds	50.1±0 seconds
* ramp.up * ate T_L to T_p	=/ , Jsecond ma-#	=/ , Jsecond ma-#
Liquidous Temperature T_L	175	175
Time t_L + aintained Abo&e T_L	50 : 10 seconds	50 : 10 seconds
ea" ;ody ac"age Temperature	175	175
Time t_p within (/ , of 50% ,	±0 seconds	±0 seconds
* amp.down * ate T_p to T_L	5 / , Jsecond ma-	5 / , Jsecond ma-
Time (/ , to ea" Temperature	5 minutes ma-#	7 minutes ma-#



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